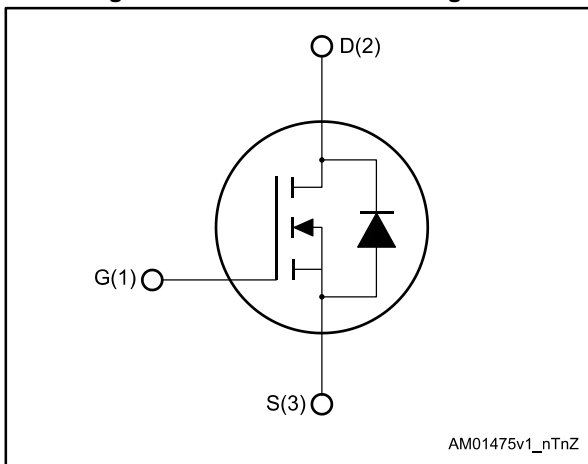


## N-channel 500 V, 0.08 $\Omega$ typ., 45 A MDmesh™ Power MOSFET in a TO-247 package

Datasheet - production data



Figure 1: Internal schematic diagram



### Features

Order code	V <sub>DS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STW45NM50	500 V	0.1 $\Omega$	45 A

- 100% avalanche tested
- High dv/dt and avalanche capabilities
- Low input capacitance and gate charge
- Low gate input resistance

### Applications

- Switching applications

### Description

This N-channel Power MOSFET is developed using STMicroelectronics' revolutionary MDmesh™ technology, which associates the multiple drain process with the company's PowerMESH™ horizontal layout. This device offer extremely low on-resistance, high dv/dt and excellent avalanche characteristics. Utilizing ST's proprietary strip technique, this Power MOSFET boasts an overall dynamic performance which is superior to similar products on the market.

Table 1: Device summary

Order code	Marking	Package	Packaging
STW45NM50	W45NM50	TO-247	Tube

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# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 30$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	45	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	28.4	A
$I_{DM}^{(1)}$	Drain current (pulsed)	180	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	390	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$T_{stg}$	Storage temperature range	-55 to 150	$^\circ\text{C}$
$T_j$	Operating junction temperature range		

**Notes:**

<sup>(1)</sup>Pulse width limited by safe operating area.

<sup>(2)</sup> $I_{SD} \leq 45\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ,  $V_{DS(\text{peak})} \leq V_{(BR)DSS}$ ,  $V_{DD} \leq 80\% V_{(BR)DSS}$

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj\text{-case}}$	Thermal resistance junction-case	0.32	$^\circ\text{C}/\text{W}$
$R_{thj\text{-amb}}$	Thermal resistance junction-ambient	30	$^\circ\text{C}/\text{W}$

**Table 4: Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_{j\text{ max}}$ )	15	A
$E_{AS}$	Single pulse avalanche energy (starting $T_J=25\text{ }^\circ\text{C}$ , $I_D=I_{AR}$ , $V_{DD}=50\text{ V}$ )	700	mJ

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 5: On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0\text{ V}$	500			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$ , $V_{DS} = 500\text{ V}$			10	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$ , $V_{DS} = 500\text{ V}$ , $T_C = 125\text{ °C}$ <sup>(1)</sup>			100	
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 30\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 22.5\text{ A}$		0.08	0.1	$\Omega$

**Notes:**

<sup>(1)</sup>Defined by design, not subject to production test.

**Table 6: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0\text{ V}$	-	3290	-	pF
$C_{oss}$	Output capacitance		-	865	-	pF
$C_{rss}$	Reverse transfer capacitance		-	140	-	pF
$C_{oss\text{ eq.}}$ <sup>(1)</sup>	Equivalent output capacitance	$V_{GS} = 0\text{ V}$ , $V_{DS} = 0\text{ to }400\text{ V}$	-	270	-	pF
$Q_g$	Total gate charge	$V_{DD} = 400\text{ V}$ , $I_D = 45\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 14: "Test circuit for gate charge behavior"</a> )	-	113	-	nC
$Q_{gs}$	Gate-source charge		-	17	-	nC
$Q_{gd}$	Gate-drain charge		-	82	-	nC
$R_G$	Gate input resistance	$f = 1\text{ MHz}$ , $I_D = 0\text{ A}$	-	1.7	-	$\Omega$

**Notes:**

<sup>(1)</sup> $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DS}$

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 250 \text{ V}$ , $I_D = 22.5 \text{ A}$ , $R_G = 4.7 \text{ } \Omega$ , $V_{GS} = 10 \text{ V}$ (see <a href="#">Figure 15: "Test circuit for inductive load switching and diode recovery times"</a> )	-	29.1	-	ns
$t_r$	Rise time		-	73.6	-	ns
$t_{r(voff)}$	Off-voltage rise time	$V_{DD} = 400 \text{ V}$ , $I_D = 45 \text{ A}$ , $R_G = 4.7 \text{ } \Omega$ , $V_{GS} = 10 \text{ V}$ (see <a href="#">Figure 15: "Test circuit for inductive load switching and diode recovery times"</a> )	-	20.8	-	ns
$t_f$	Fall time		-	58.3	-	ns
$t_c$	Cross-over time		-	67.6	-	ns

Table 8: Source-drain diode

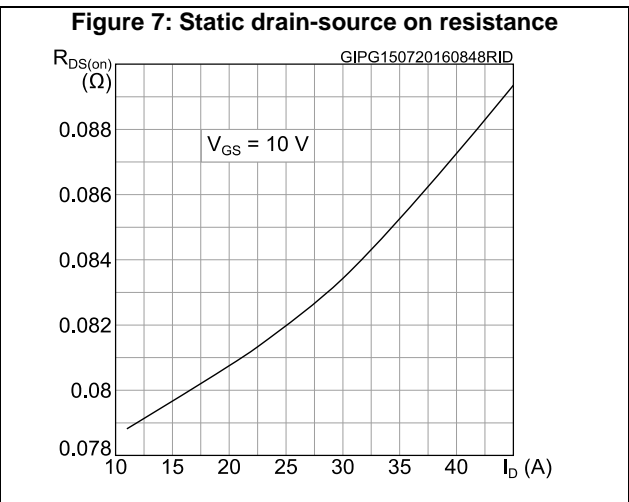
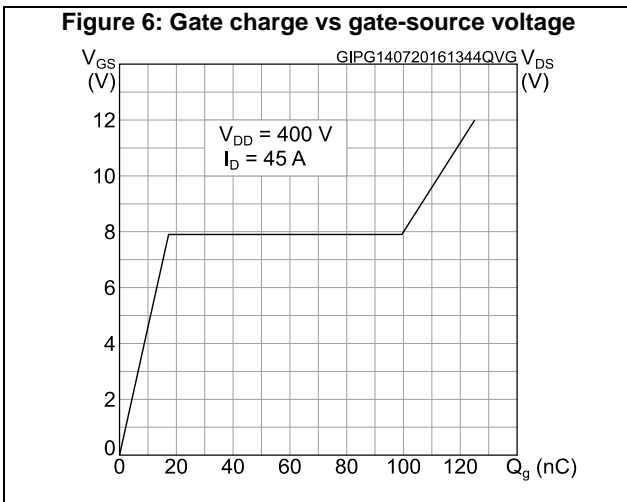
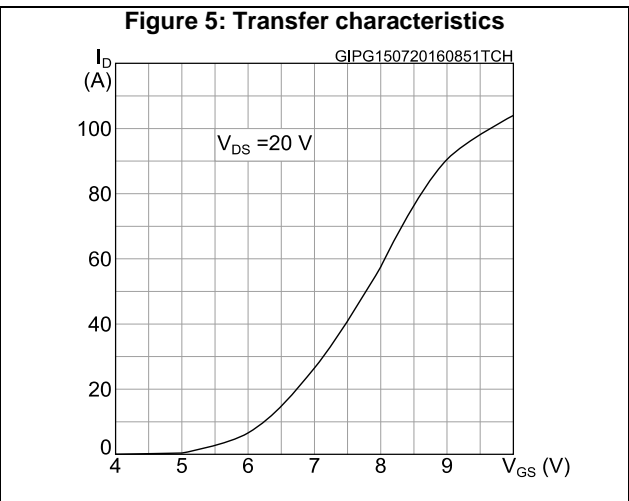
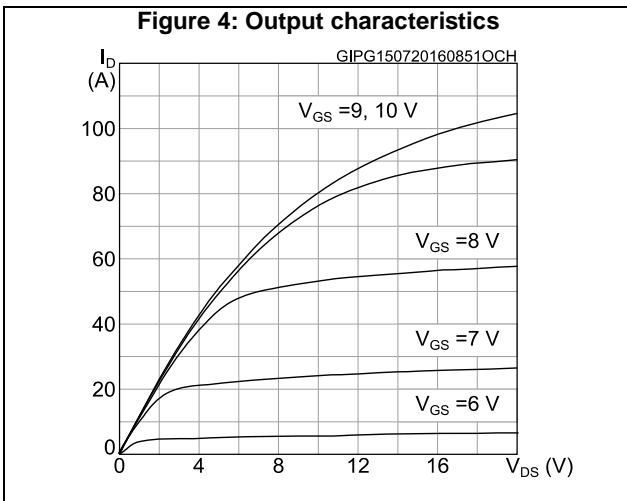
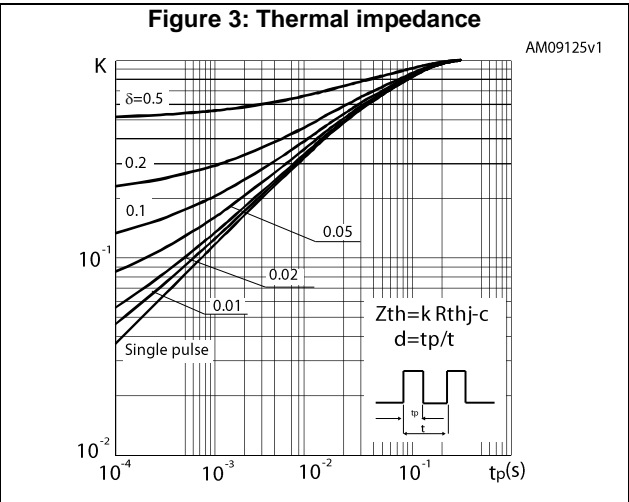
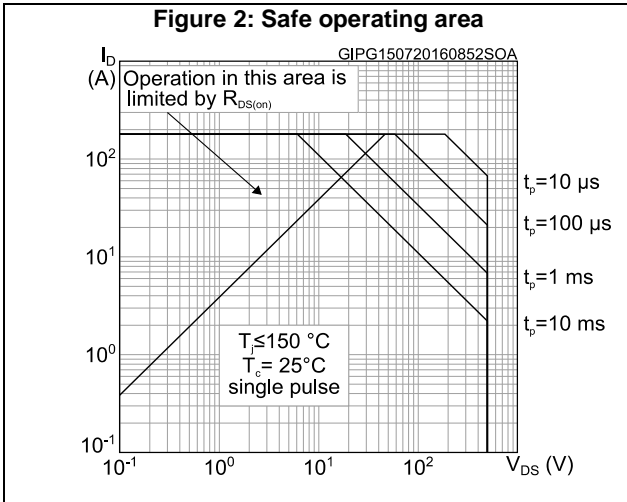
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		45	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		180	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 45 \text{ A}$ , $V_{GS} = 0 \text{ V}$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 45 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$	-	454		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 60 \text{ V}$ (see <a href="#">Figure 15: "Test circuit for inductive load switching and diode recovery times"</a> )	-	9380		nC
$I_{RRM}$	Reverse recovery current		-	41.3		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 45 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$	-	567		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 100 \text{ V}$ , $T_j = 150 \text{ } ^\circ\text{C}$ (see <a href="#">Figure 15: "Test circuit for inductive load switching and diode recovery times"</a> )	-	12700		nC
$I_{RRM}$	Reverse recovery current		-	44.8		A

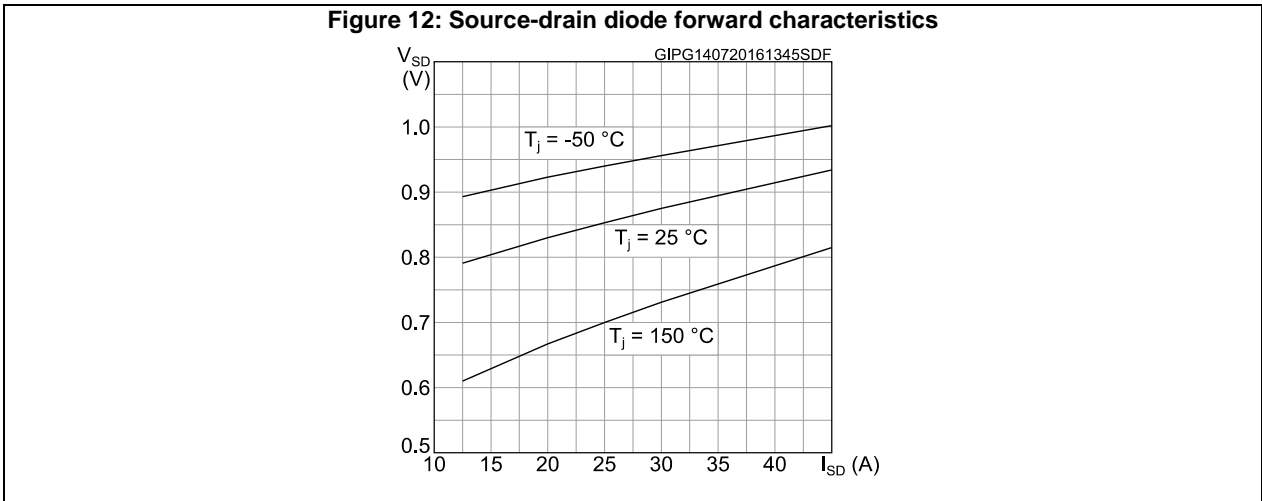
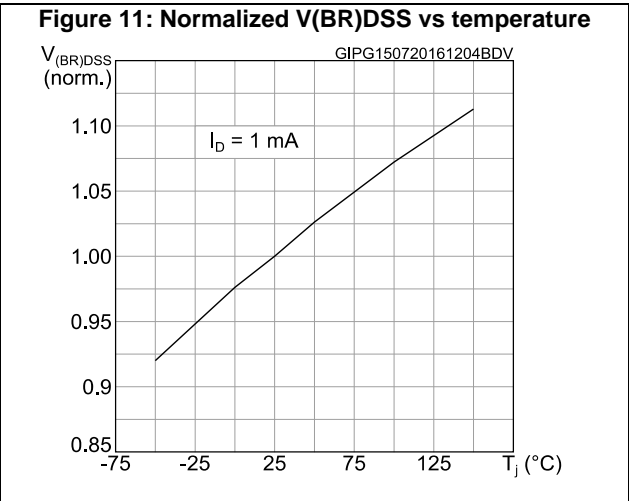
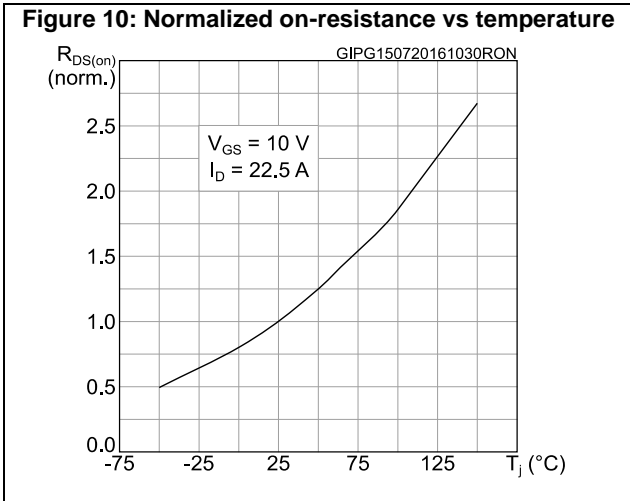
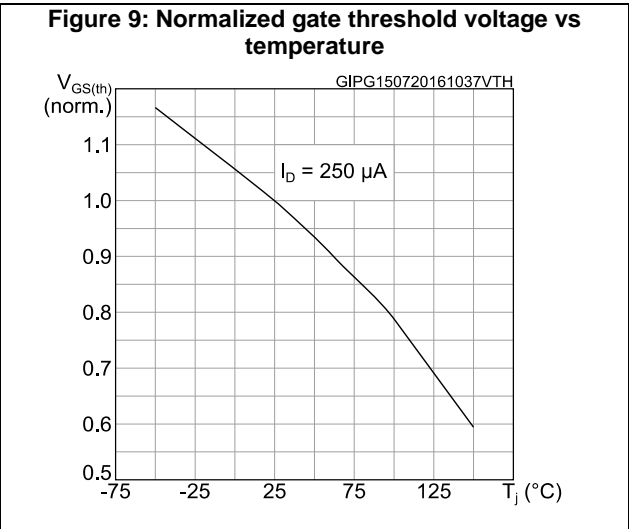
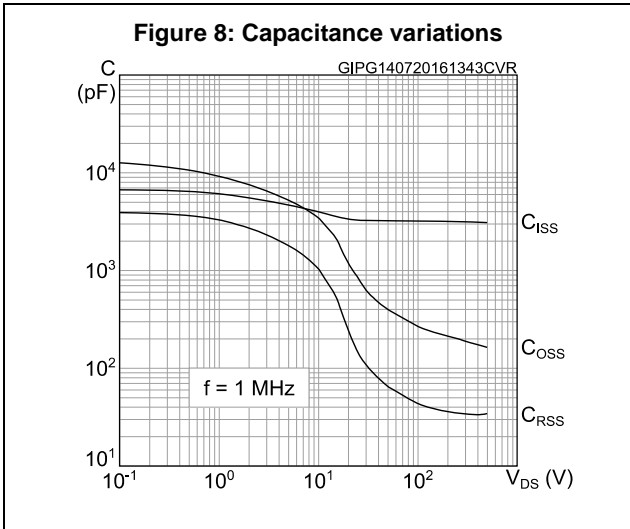
**Notes:**

(1) Pulse width limited by safe operating area.

(2) Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

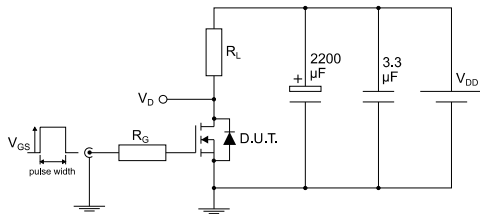
## 2.1 Electrical characteristics (curves)





### 3 Test circuits

**Figure 13: Test circuit for resistive load switching times**



AM01468v1

**Figure 14: Test circuit for gate charge behavior**



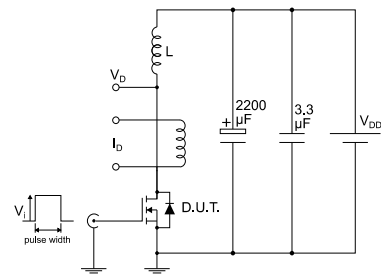
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**Figure 15: Test circuit for inductive load switching and diode recovery times**



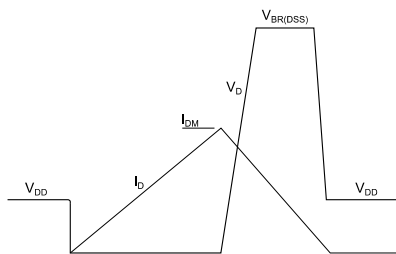
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**Figure 16: Unclamped inductive load test circuit**



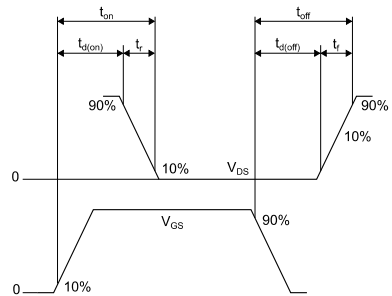
AM01471v1

**Figure 17: Unclamped inductive waveform**



AM01472v1

**Figure 18: Switching time waveform**



AM01473v1



## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 TO-247 package information

Figure 19: TO-247 package outline

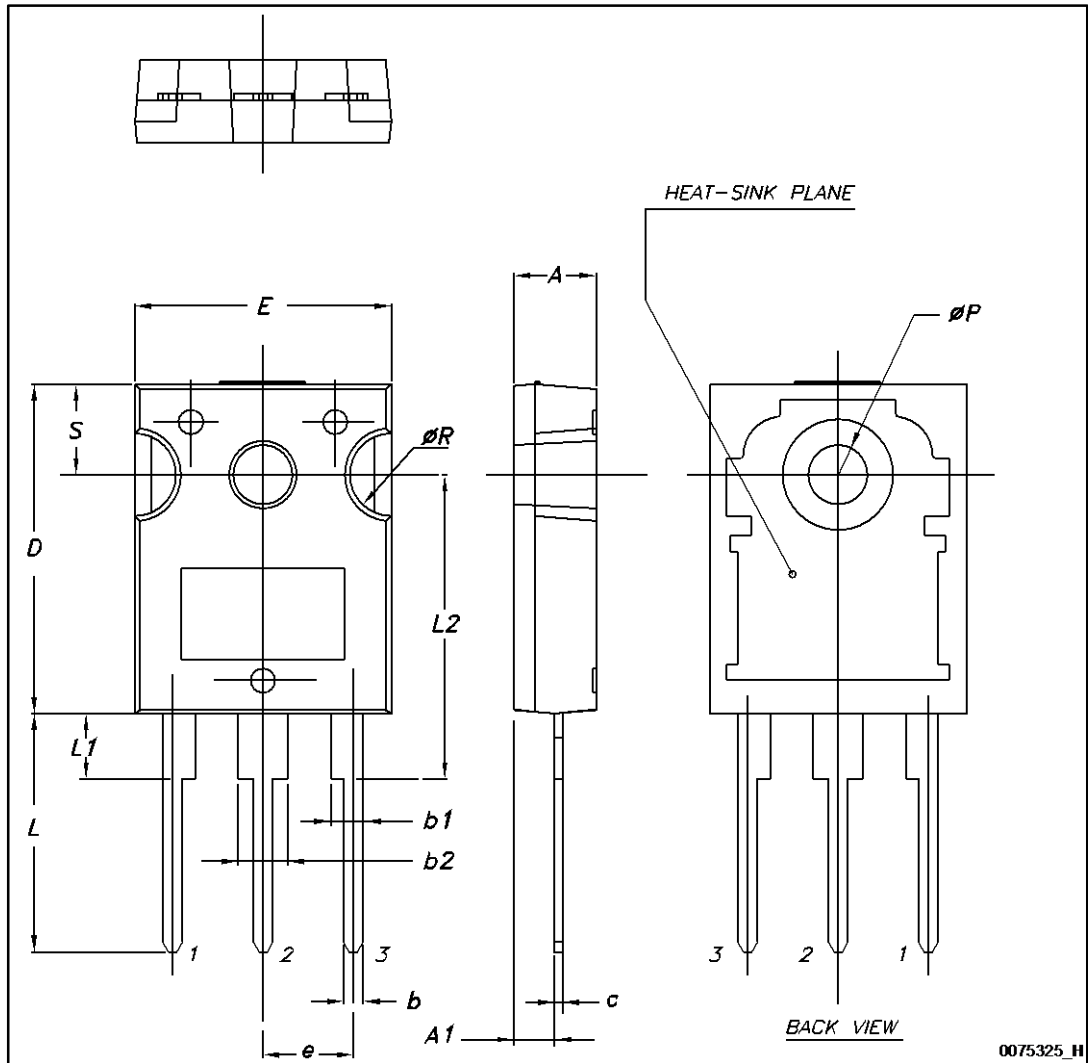


Table 9: TO-247 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

## 5 Revision history

**Table 10: Document revision history**

Date	Revision	Changes
30-Mar-2005	4	Modified value on <i>Source drain diode</i>
23-Jul-2009	5	Modified values on <i>Switching times</i>
18-Jul-2016	6	Modified: <i>Table 2: "Absolute maximum ratings"</i> , <i>Table 3: "Thermal data"</i> , <i>Table 4: "Avalanche characteristics"</i> , <i>Table 5: "On/off states"</i> , <i>Table 6: "Dynamic"</i> , <i>Table 7: "Switching times"</i> and <i>Table 8: "Source-drain diode"</i> Modified: <i>Section 5.1: "Electrical characteristics (curves)"</i> Updated: <i>Section 7.1: "TO-247 package information"</i>

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